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APPLICATION NO.	1	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/768,238	•	01/29/2004	Toshitake Yaegashi	81790.0311	6199	
26021	7590	05/02/2005		EXAM	EXAMINER	
HOGAN & HARTSON L.L.P.				WILSON,	WILSON, ALLAN R	
500 S. GRA SUITE 1900		NUE		ART UNIT	PAPER NUMBER	
LOS ANGELES, CA 90071-2611				2815	-	
				DATE MAILED: 05/02/200	5	

Please find below and/or attached an Office communication concerning this application or proceeding.

		Application No.	Applicant(s)				
		10/768,238	YAEGASHI ET AL.				
	Office Action Summary	Examiner	Art Unit				
		Allan R. Wilson	2815				
Period fo	The MAILING DATE of this communication or Reply	n appears on the cover sheet w	th the correspondence address				
THE - External form of the control o	ORTENED STATUTORY PERIOD FOR RIMAILING DATE OF THIS COMMUNICATION IN THE PROVISION OF THIS COMMUNICATION IN THE PROVISION OF	ON. FR 1.136(a). In no event, however, may a in. a reply within the statutory minimum of thir eriod will apply and will expire SIX (6) MON statute, cause the application to become AF	eply be timely filed  y (30) days will be considered timely.  THS from the mailing date of this communic  ANDONED (35 U.S.C. § 133).	cation.			
Status							
1)⊠	Responsive to communication(s) filed on	29 January 2004.					
		This action is non-final.					
3)□	<i>/</i>						
Dispositi	ion of Claims						
5)□ 6)⊠ 7)□	Claim(s) 17-20 is/are pending in the application of the above claim(s) is/are with Claim(s) is/are allowed.  Claim(s) 17-20 is/are rejected.  Claim(s) is/are objected to.  Claim(s) are subject to restriction a	ndrawn from consideration.					
Applicati	on Papers		•				
9)[	The specification is objected to by the Exam	miner.					
10)	☐ The drawing(s) filed on is/are: a)☐ accepted or b)☐ objected to by the Examiner.						
	Applicant may not request that any objection to						
11)	Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).  The oath or declaration is objected to by the Examiner. Note the attached Office Action or form.PTO-152.						
	Inder 35 U.S.C. § 119	C Examiner. Note the attached	Office Action of John 1 TO-102				
_	•		4404 ) (1) (2)				
a)[	<ul> <li>Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).</li> <li>□ All b) □ Some * c) □ None of:</li> <li>1. □ Certified copies of the priority documents have been received.</li> <li>2. □ Certified copies of the priority documents have been received in Application No. 09/112,482.</li> <li>3. □ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).</li> <li>See the attached detailed Office action for a list of the certified copies not received.</li> </ul>						
Attachment	i(s)		-				
	e of References Cited (PTO-892)		ummary (PTO-413)				
3) 🛛 Infom	e of Draftsperson's Patent Drawing Review (PTO-948 nation Disclosure Statement(s) (PTO-1449 or PTO/SE r No(s)/Mail Date <u>01/29/2004</u> .		)/Mail Date formal Patent Application (PTO-152) 				

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## **DETAILED ACTION**

## Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

Claims 17-20 are rejected under 35 USC § 102(b) as being anticipated by Japanese Patent Application No. 8-23041 ("JP '041") disclosed by Applicants.

With regards to claim 17, JP '041 illustrates in figures 1-17, particularly figures 1-7, (entire document) forming, on a first region 5 of a semiconductor substrate 1, a self-aligned double-layer gate structure which includes a gate insulating film 10, a first conductor 11 serving as a floating gate layer, a second conductor 13 serving as a control gate layer, and an insulating film 12 electrically insulating the first and second conductors,

patterning the first conductor into a gate electrode of a transistor above a second region 6 of the semiconductor substrate; and

providing a third conductor 21 on the first conductor patterned in a form of the gate electrode above the second region.

With regards to claim 18, JP '041 illustrates in figs. 1-7 sequentially forming, on a semiconductor substrate 1, a gate insulating film 10, a first conductor 11 serving as a floating gate layer, an insulating film 12, and a second conductor 13 serving as a control gate layer;

patterning the second conductor, the insulating film and the first conductor in a selfaligned manner in a first region 5 of the semiconductor substrate, using a single mask, thereby forming a double-layer gate structure (fig. 3), and removing that portion of the second conductor which is provided on a second region of the semiconductor substrate during the patterning of the second conductor in the first region (fig. 4);

forming a third conductor 21 on the first conductor in the second region 6 after the patterning of the first conductor in the first region, such that the first and third conductors are electrically connected to each other; and

patterning the third and first conductors into a gate electrode of a transistor in the second region.

With regards to claims 19 and 20, JP '041 illustrates in figs. 1-7 forming an element isolating region 3 (in region 5) adjacent to the transistor, and forming the double-layer gate structure on the element isolating region.

## Conclusion

The prior art made of record and not relied upon is considered pertinent to applicant's disclosure: Kono et al. and Mazzali (illustrate a memory device with dual gate and single gate transistors).

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Field of Search	Date
U.S. Class and subclass:	
257/201, 211, 257, 275	April 29, 2005
Other Documentation:	
None	N/A
Electronic data base(s):	
EAST (USPAT, US-PGPUB, JPO, EPO, Derwent, IBM TDB)	April 29, 2005

Any inquiry concerning this communication or earlier communications from an examiner should be directed to Primary Examiner Allan Wilson whose telephone number is (571) 272-1738. Examiner Wilson can normally be reached 7:00-4:00 Monday-Thursday and 6:00-3:00 on Friday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Tom Thomas can be reached on (571) 272-1664. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Allan R. Wilson Primary Examiner

29 April 2005

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